GCS GaAs PIN Photodiodes for 10Gb/s 1x4, 1x8, 1x12 Array Applications

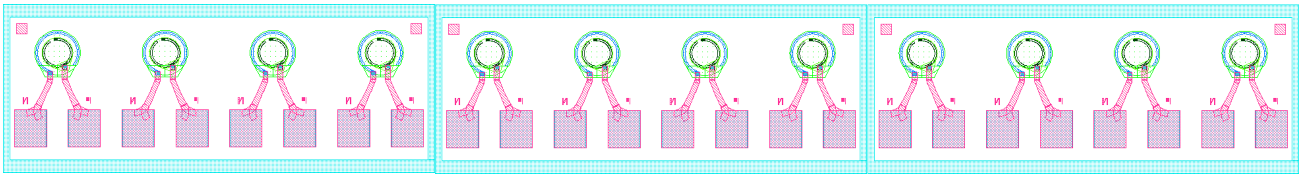
850 nm GaAs PIN PD

- **Mesa Diode on Semi-Insulating Substrates**
- **Anode/Cathode Bonding Pads on Front Side**
- **Low Dark Current & Capacitance with High Responsivity**
- **Bandwidths up to 10 GHz**
- **Customer Specified Configurations Available**

Part Number: Do186-60um-PIN4-1x4,8,12	
PHYSICAL	**Typical**
Aperture Dia.	60 µm
Bonding Pad Dia.	75 µm x 90 µm
Die Height	150 µm
Die Size	(1-3 mm) X 400 µm
Substrate	Semi-Insulating

Applications

- **850nm 10G 1x4, 1x8, 1x12**
- **Infiniband**
- **SONET/SDH**
- **Unsealed 85 R.H./85C Qualified**



Key Benefits

- **Low-Cost 4-inch Manufacturing**
- **Fast Cycle-Times**
- **CAD Support & Mask Procurement**
- **Robust Process**

Mask ID: Do186 (60µm)						
CHARACTERISTICS	**Conditions**	**Min.**	**Typical**	**Max**	**Unit**	**Notes**
Bandwidth	-3V	-	10	-	GHz	
Wavelength Range	-3V	760	850	860	nm	
Responsivity	-3V	0.5	0.6	-	A/W	@ 850nm
Dark Current	-3V	-	0.1	0.5	nA	
Reverse Breakdown	-20V	-	-	1	µA	
Capacitance	-3V	-	0.20	0.23	pF	

Global Communication Semiconductors, Inc
23155 Kashiwa Court, Torrance, CA 90505
Tel: (310) 530-7274 Fax: (310) 517-8200 e-mail: info@gcsincorp.com
www.gcsincorp.com

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